

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	Wafer Vendor
	5.0	Overall Thickness	465.00 +/- 15.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00 μ m	Guaranteed by Process
	7.0	Bow	<120.00 μ m	Estimate ADE to ASTM F534, 100%
	8.0	Warp	<120.00 μ m	Estimate
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 10.00 μ m	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1 ~ 20 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with lasermark and oxide.	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and / or device wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	23.0	Nominal Thickness	7.00 +/- 0.50 μ m	FTIR, 100% 9-Pt (note3)
	24.0	Device Doping Type	P	Wafer Vendor
	25.0	Device Dopant	Boron	Wafer Vendor
	26.0	Device Resistivity	1 ~ 20 Ohmcm	Wafer Vendor
BuriedOxide2	27.0	Oxide 2 formed on	Handle and/or Device silicon	Guaranteed by process
	28.0	Oxide 2 Thickness	10,000.00 +/- 500.00 A	FTIR, 100% 9-Pt (note3)
	29.0	Oxide 2 Type	Thermal Oxide	Guaranteed by process
DeviceSilicon2	30.0	Device 2 Growth Method	CZ	Wafer Vendor
	31.0	Device 2 Orientation	{100} +/- 1.0degree	Wafer Vendor
	32.0	Device 2 Nominal Thickness	3.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note3)
	33.0	Device 2 Resistivity	1 ~ 20 Ohmcm	Wafer vendor
	34.0	Device 2 DopingType	P	Wafer vendor
	35.0	Device 2 Dopant	Boron	Wafer vendor
BuriedOxide3	36.0	Oxide 3 formed on	Handle and / or Device silicon	Guaranteed by process

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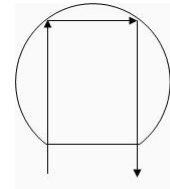
Customer

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BuriedOxide3	37.0 Oxide 3 Thickness	10,000.00 +/- 500.00 A	FTIR, 100% 9-Pt (note3)
	38.0 Oxide 3 Type	Thermal Oxide	Guaranteed by process
DeviceSilicon3	39.0 Device 3 Growth Method	CZ	Wafer Vendor
	40.0 Device 3 Orientation	{100} +/- 1.0degree	Wafer Vendor
	41.0 Device 3 Nominal Thickness	51.00 +/- 1.50 um	FTIR, 100% 9-Pt (note3)
	42.0 Device 3 Resistivity	0.001 ~ 0.005 Ohm cm	Wafer Vendor
	43.0 Device 3 DopingType	P	Wafer Vendor
	44.0 Device 3 Dopant	Boron	Wafer Vendor

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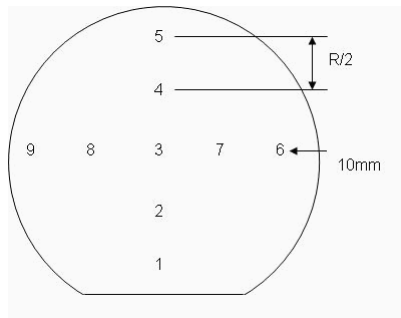
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information